



N-CHANNEL ENHANCEMENT MODE MOSFET

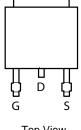
Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

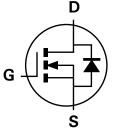
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 🔞
- Weight: 0.33 grams (approximate)





D

Top View Pin-Out



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMG4800LK3-13	TO252	2500 / Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>

4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



>!! = Manufacturer's Marking
N4800L = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 09 = 2009)
WW = Week (01 - 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 5)	Steady State	T _A = +25°C T _A = +85°C	ID	10.0 6.5	A
Pulsed Drain Current (Note 6)			I _{DM}	48	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	1.71	W
Thermal Resistance, Junction to Ambient @T _A = +25°C	R _{0JA}	72.9	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	-	1.0	μA	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(th)}	0.8	-	1.6	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance			12	17	mΩ	$V_{GS} = 10V, I_D = 9A$	
	R _{DS (ON)}	-	16	24	11122	$V_{GS} = 4.5V, I_D = 7A$	
Forward Transfer Admittance	Y _{fs}	-	10	-	S	$V_{DS} = 10V, I_{D} = 9A$	
Diode Forward Voltage	V _{SD}	-	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	-	798	-	pF		
Output Capacitance	Coss	-	128	-	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	Crss	-	122	-	pF	T = T.000172	
Gate Resistance	Rg	-	1.37	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge	Qg	-	8.7	-	nC	V _{GS} = 5V, V _{DS} = 15V, I _D = 9A	
Gate-Source Charge	Q _{gs}	-	1.7	-	nC		
Gate-Drain Charge	Q _{gd}	-	2.4	-	nC	$I_D = 9A$	
Turn-On Delay Time	t _{D(on)}	-	5.03	-	ns		
Turn-On Rise Time	tr	-	4.50	-	ns	$\label{eq:VDD} \begin{split} V_{DD} &= 15V, \ V_{GS} = 10V, \\ R_L &= 15\Omega, \ R_G = 6\Omega, \ I_D = 1A \end{split}$	
Turn-Off Delay Time	t _{D(off)}	-	26.33	-	ns		
Turn-Off Fall Time	t _f	-	8.55	-	ns		

Notes:

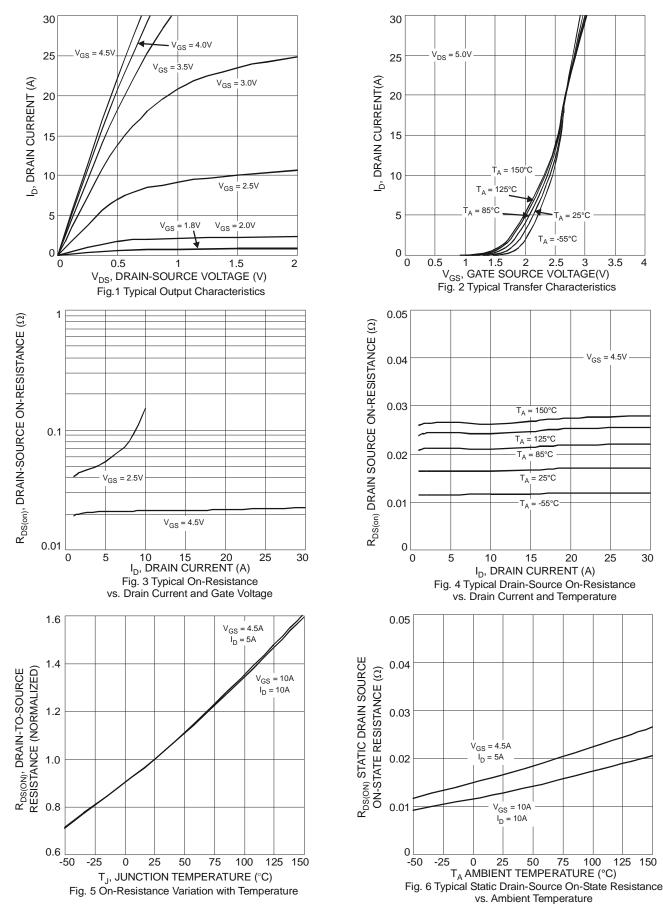
5. Device mounted on FR-4 PCB, with minimum recommended pad layout.

6. Repetitive rating, pulse width limited by junction temperature.

Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.

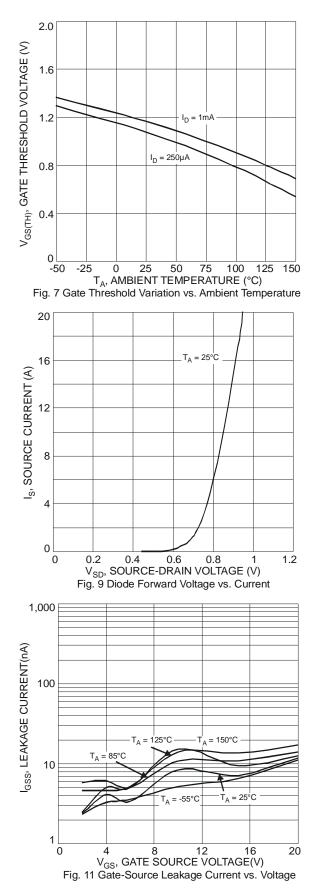


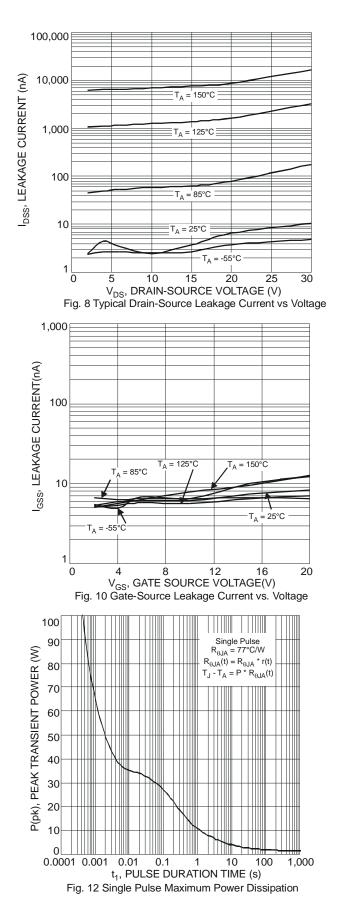
DMG4800LK3



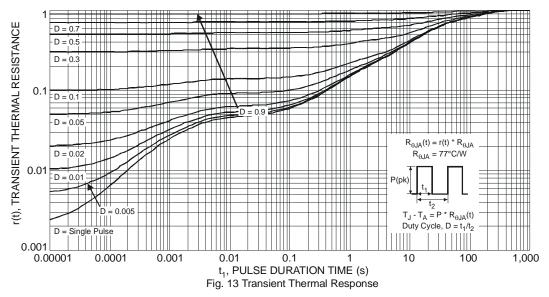
DMG4800LK3





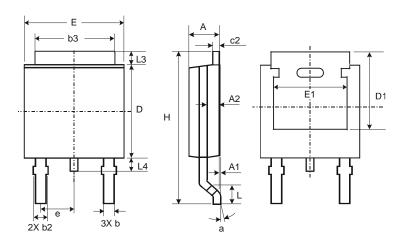






Package Outline Dimensions

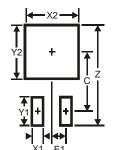
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



TO252					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
c2	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	_	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	_		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	11.6
X1	1.5
X2	7.0
Y1	2.5
Y2	7.0
С	6.9
E1	2.3



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